

SUPPLEMENTARY INFORMATION

High-resolution organic field-effect transistors manufactured by electrohydrodynamic inkjet printing of doped electrodes

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SUPPLEMENTARY FIGURES

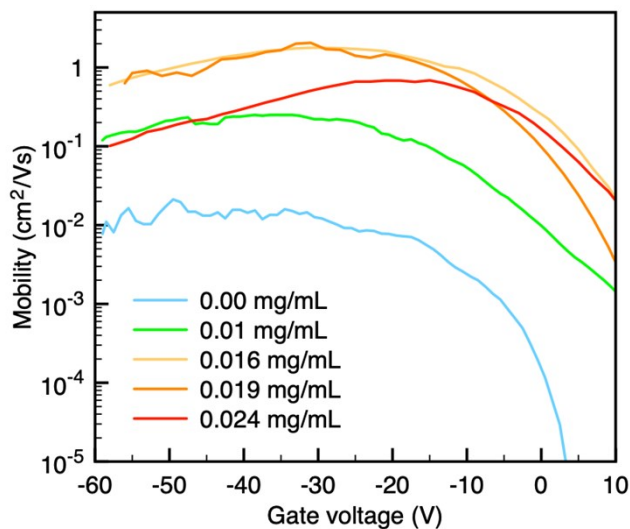


Fig. S1. Field-effect mobility of the OFET as a function of gate voltage.

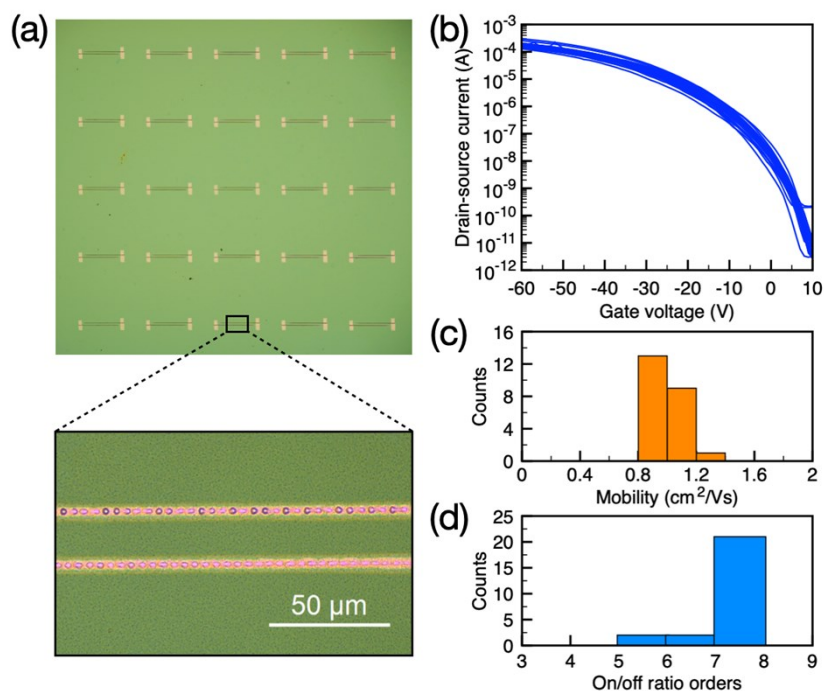


Fig. S2. (a) Optical microscopy image of the printed DNTT 5×5 array, inset is zoomed-in image of printed electrodes, the channel width and length of printed OFETs is 300 and 15 μm , respectively. (b) 25 transfer I-V curves of the 5×5 devices array. (c) A histogram of the saturation mobility of 25 OFETs. (d) A histogram of the on/off current ratio of 25 OFETs.